

INTRODUCE:

HVGT Half Bridge high voltage silicon rectifier assembly is made of high quality silicon GPP chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Ultra high frequency.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. HV rectification, isolation, protection.
2. High voltage testing equipment.
3. High voltage rectifier used in electrostatic cleaning.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes M5.
3. Net weight: 340.0 grams (approx).

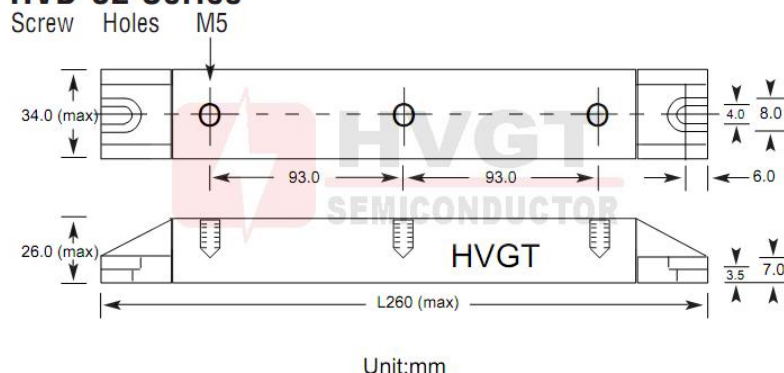
SHAPE DISPLAY:



SIZE: (Unit:mm)

HVGT NAME: HVD-32

HVD-32 Series

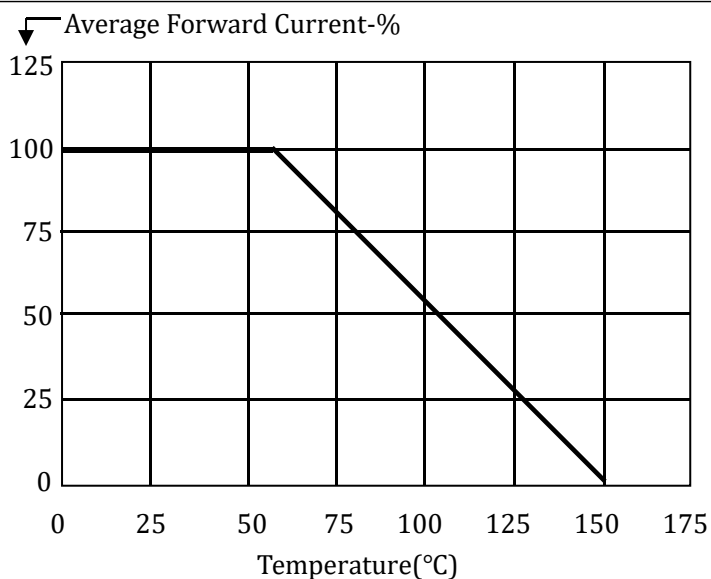
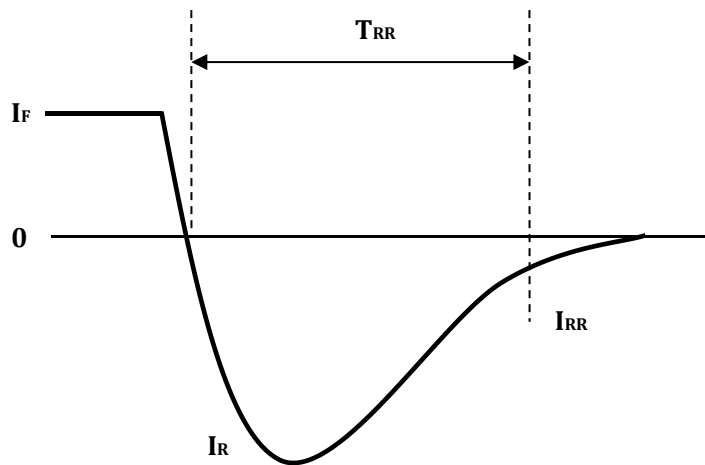
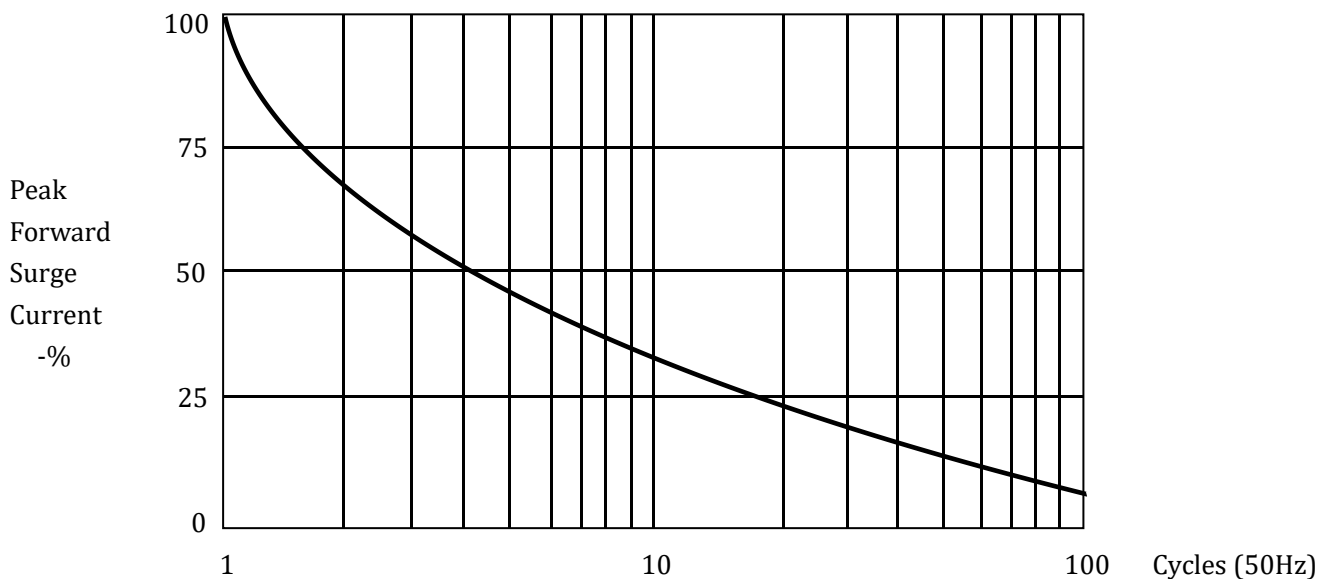


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value		Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$; $I_R=5.0\mu A$	36	36	kV
Peak Working Reverse Voltage	V_{RWM}	$T_A=25^{\circ}C$; $I_R=5.0\mu A$	36	36	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$; $I_R=100\mu A$	40	40	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=55^{\circ}C$; 50Hz Half-sine Wave; Resistance load	2.0		A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3ms	50		A
Junction Temperature	T_J		150		$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+150		$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value		Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	70	70	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	10		μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	100		μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	100		nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--		pF

Forward Current Derating Curve

Reverse Recovery Measurement Waveform

Non-Repetitive Surge Current

MARKING:

Marking	Type	Code	Cathode Mark
	HBG020D360G	HBG020D360G HVGT	

PART NUMBER NOTE:

Type	Chip	$I_{F(AV)}$	Frequency	V_{RRM}	T_{RR}
HB	G	020	D	360	G
Half Bridge Series	GPP Chip	2.0A	D=Doubler. P=Positive Center Tap. N=Negative Center Cap.	36kV	(U)75ns (G)100ns (D) Standard Recovery Time